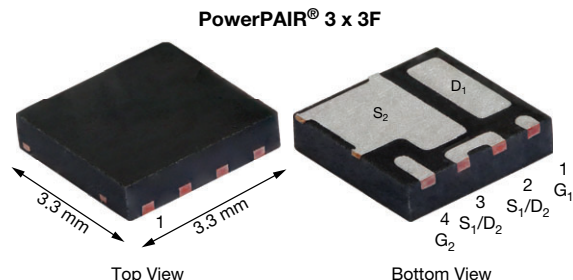


## Dual N-Channel 30 V (D-S) MOSFET with Schottky Diode



## PRODUCT SUMMARY

|                                                         | CHANNEL-1 | CHANNEL-2 |
|---------------------------------------------------------|-----------|-----------|
| V <sub>DS</sub> (V)                                     | 30        | 30        |
| R <sub>DS(on)</sub> max. (Ω) at V <sub>GS</sub> = 10 V  | 0.00450   | 0.00184   |
| R <sub>DS(on)</sub> max. (Ω) at V <sub>GS</sub> = 4.5 V | 0.00700   | 0.00257   |
| Q <sub>g</sub> typ. (nC)                                | 6.9       | 19.4      |
| I <sub>D</sub> (A) <sup>a</sup>                         | 75        | 141       |
| Configuration                                           | Dual      |           |

## ORDERING INFORMATION

|                                 |                  |
|---------------------------------|------------------|
| Package                         | PowerPAIR 3 x 3F |
| Lead (Pb)-free and halogen-free | SiZF300DT-T1-GE3 |

**ABSOLUTE MAXIMUM RATINGS** ( $T_A = 25\text{ }^{\circ}\text{C}$ , unless otherwise noted)

| PARAMETER                                                    |                        | SYMBOL                            | CHANNEL-1           | CHANNEL-2           | UNIT |
|--------------------------------------------------------------|------------------------|-----------------------------------|---------------------|---------------------|------|
| Drain-source voltage                                         |                        | V <sub>DS</sub>                   | 30                  | 30                  | V    |
| Gate-source voltage                                          |                        | V <sub>GS</sub>                   | +20, -16            | +16, -12            |      |
| Continuous drain current (T <sub>J</sub> = 150 °C)           | T <sub>C</sub> = 25 °C | I <sub>D</sub>                    | 75                  | 141                 | A    |
|                                                              | T <sub>C</sub> = 70 °C |                                   | 60                  | 113                 |      |
|                                                              | T <sub>A</sub> = 25 °C |                                   | 23 <sup>b, c</sup>  | 34 <sup>b, c</sup>  |      |
|                                                              | T <sub>A</sub> = 70 °C |                                   | 18 <sup>b, c</sup>  | 27 <sup>b, c</sup>  |      |
| Pulsed drain current (t = 100 μs)                            |                        | I <sub>DM</sub>                   | 150                 | 200                 |      |
| Continuous source-drain diode current                        | T <sub>C</sub> = 25 °C | I <sub>S</sub>                    | 44                  | 105                 |      |
|                                                              | T <sub>A</sub> = 25 °C |                                   | 3,4 <sup>b, c</sup> | 6,2 <sup>b, c</sup> |      |
| Single pulse avalanche current                               | L = 0.1 mH             | I <sub>AS</sub>                   | 14                  | 16                  | mJ   |
| Single pulse avalanche energy                                |                        | E <sub>AS</sub>                   | 9.8                 | 12.8                |      |
| Maximum power dissipation                                    | T <sub>C</sub> = 25 °C | P <sub>D</sub>                    | 48                  | 74                  | W    |
|                                                              | T <sub>C</sub> = 70 °C |                                   | 31                  | 47                  |      |
|                                                              | T <sub>A</sub> = 25 °C |                                   | 3.8 <sup>b, c</sup> | 4.3 <sup>b, c</sup> |      |
|                                                              | T <sub>A</sub> = 70 °C |                                   | 2.4 <sup>b, c</sup> | 2.8 <sup>b, c</sup> |      |
| Operating junction and storage temperature range             |                        | T <sub>J</sub> , T <sub>stg</sub> | -55 to +150         |                     | °C   |
| Soldering recommendations (peak temperature) <sup>d, e</sup> |                        |                                   | 260                 |                     |      |

## THERMAL RESISTANCE RATINGS

| PARAMETER                                   |              | SYMBOL            | CHANNEL-1 |      | CHANNEL-2 |      | UNIT |
|---------------------------------------------|--------------|-------------------|-----------|------|-----------|------|------|
|                                             |              |                   | TYP.      | MAX. | TYP.      | MAX. |      |
| Maximum junction-to-ambient <sup>b, f</sup> | t ≤ 10 s     | R <sub>thJA</sub> | 26        | 33   | 23        | 29   | °C/W |
| Maximum junction-to-case (source)           | Steady state | R <sub>thJC</sub> | 2         | 2.6  | 1.3       | 1.7  |      |

## Notes

a.  $T_C = 25^\circ\text{C}$

b. Surface mounted on 1" x 1" FR4 board

c.  $t = 10 \text{ s}$

d. See solder profile ([www.vishay.com/doc?73257](http://www.vishay.com/doc?73257)). The PowerPAIR 3 x 3F is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

f. Maximum under steady state conditions is 66 °C/W for channel-1 and 67 °C/W for channel-2

## FEATURES

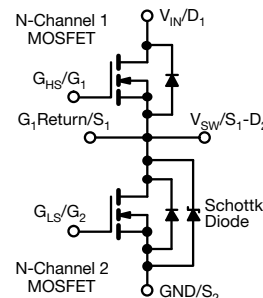
- TrenchFET® Gen IV power MOSFET
- SkyFET® low side MOSFET with integrated Schottky
- 100 % R<sub>g</sub> and UIS tested
- Internally connected half-bridge configuration in 3.3 mm-by-3.3 mm footprint
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**

## APPLICATIONS

- CPU core power
- Computer / server peripherals
- POL
- Synchronous buck converter
- Telecom DC/DC





| SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted) |                     |                                                                                                                                   |                                                                                                                                   |      |         |         |       |     |
|-----------------------------------------------------------------|---------------------|-----------------------------------------------------------------------------------------------------------------------------------|-----------------------------------------------------------------------------------------------------------------------------------|------|---------|---------|-------|-----|
| PARAMETER                                                       | SYMBOL              | TEST CONDITIONS                                                                                                                   |                                                                                                                                   | MIN. | TYP.    | MAX.    | UNIT  |     |
| Static                                                          |                     |                                                                                                                                   |                                                                                                                                   |      |         |         |       |     |
| Drain-source breakdown voltage                                  | V <sub>DS</sub>     | V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA                                                                                    | Ch-1                                                                                                                              | 30   | -       | -       | V     |     |
|                                                                 |                     |                                                                                                                                   | Ch-2                                                                                                                              | 30   | -       | -       |       |     |
| Gate-source threshold voltage                                   | V <sub>GS(th)</sub> | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA                                                                       | Ch-1                                                                                                                              | 1.1  | -       | 2.2     |       |     |
|                                                                 |                     |                                                                                                                                   | Ch-2                                                                                                                              | 1.0  | -       | 2.2     |       |     |
| Gate-source leakage                                             | I <sub>GSS</sub>    | V <sub>DS</sub> = 0 V, V <sub>GS</sub> = +20 V, -16 V                                                                             | Ch-1                                                                                                                              | -    | -       | ± 100   | nA    |     |
|                                                                 |                     | V <sub>DS</sub> = 0 V, V <sub>GS</sub> = +16 V, -12 V                                                                             | Ch-2                                                                                                                              | -    | -       | ± 100   |       |     |
| Zero Gate voltage drain current                                 | I <sub>DSS</sub>    | V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V                                                                                     | Ch-1                                                                                                                              | -    | -       | 1       | μA    |     |
|                                                                 |                     |                                                                                                                                   | Ch-2                                                                                                                              | -    | 30      | 350     |       |     |
|                                                                 |                     | V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 55 °C                                                             | Ch-1                                                                                                                              | -    | -       | 5       |       |     |
|                                                                 |                     |                                                                                                                                   | Ch-2                                                                                                                              | -    | 150     | 3000    |       |     |
| On-state drain current <sup>b</sup>                             | I <sub>D(on)</sub>  | V <sub>DS</sub> ≥ 5 V, V <sub>GS</sub> = 10 V                                                                                     | Ch-1                                                                                                                              | 10   | -       | -       | A     |     |
|                                                                 |                     |                                                                                                                                   | Ch-2                                                                                                                              | 10   | -       | -       |       |     |
| Drain-source on-state resistance <sup>b</sup>                   | R <sub>DS(on)</sub> | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A                                                                                     | Ch-1                                                                                                                              | -    | 0.00330 | 0.00450 | Ω     |     |
|                                                                 |                     | V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A                                                                                     | Ch-2                                                                                                                              | -    | 0.00160 | 0.00184 |       |     |
|                                                                 |                     | V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 7 A                                                                                     | Ch-1                                                                                                                              | -    | 0.00490 | 0.00700 |       |     |
|                                                                 |                     | V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 7 A                                                                                     | Ch-2                                                                                                                              | -    | 0.00210 | 0.00257 |       |     |
| Forward transconductance <sup>b</sup>                           | g <sub>fs</sub>     | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 20 A                                                                                     | Ch-1                                                                                                                              | -    | 60      | -       | S     |     |
|                                                                 |                     | V <sub>DS</sub> = 10 V, I <sub>D</sub> = 20 A                                                                                     | Ch-2                                                                                                                              |      | 90      | -       |       |     |
| Dynamic <sup>a</sup>                                            |                     |                                                                                                                                   |                                                                                                                                   |      |         |         |       |     |
| Input capacitance                                               | C <sub>iss</sub>    | Channel-1<br>V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0 V, f = 1 MHz                                                             | Ch-1                                                                                                                              | -    | 1100    | -       | pF    |     |
|                                                                 |                     |                                                                                                                                   | Ch-2                                                                                                                              | -    | 3150    | -       |       |     |
| Output capacitance                                              | C <sub>oss</sub>    |                                                                                                                                   | Channel-2<br>V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0 V, f = 1 MHz                                                             | Ch-1 | -       | 530     |       | -   |
|                                                                 |                     |                                                                                                                                   |                                                                                                                                   | Ch-2 | -       | 1550    |       | -   |
| Reverse transfer capacitance                                    | C <sub>rss</sub>    | Channel-1<br>V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0 V, f = 1 MHz                                                             |                                                                                                                                   | Ch-1 | -       | 40      | -     |     |
|                                                                 |                     |                                                                                                                                   |                                                                                                                                   | Ch-2 | -       | 170     | -     |     |
| C <sub>rss</sub> /C <sub>iss</sub> ratio                        |                     |                                                                                                                                   |                                                                                                                                   | Ch-1 | -       | 0.036   | 0.072 |     |
|                                                                 |                     |                                                                                                                                   |                                                                                                                                   | Ch-2 | -       | 0.054   | 0.108 |     |
| Total gate charge                                               | Q <sub>g</sub>      | V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A                                                             | Ch-1                                                                                                                              | -    | 14.4    | 22      | nC    |     |
|                                                                 |                     |                                                                                                                                   | Ch-2                                                                                                                              | -    | 41      | 62      |       |     |
| Gate-source charge                                              | Q <sub>gs</sub>     | Channel-1<br>V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 10 A                                               | Ch-1                                                                                                                              | -    | 6.9     | 10.5    |       |     |
|                                                                 |                     |                                                                                                                                   | Ch-2                                                                                                                              | -    | 19.4    | 29      |       |     |
| Gate-drain charge                                               | Q <sub>gd</sub>     | Channel-1<br>V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 10 A                                               | Ch-1                                                                                                                              | -    | 3.1     | -       |       |     |
|                                                                 |                     |                                                                                                                                   | Ch-2                                                                                                                              | -    | 7.1     | -       |       |     |
| Gate-drain charge                                               | Q <sub>gd</sub>     | Channel-2<br>V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 10 A                                               | Ch-1                                                                                                                              | -    | 1.5     | -       |       |     |
|                                                                 |                     |                                                                                                                                   | Ch-2                                                                                                                              | -    | 3.8     | -       |       |     |
| Output charge                                                   | Q <sub>oss</sub>    | V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0 V                                                                                     | Ch-1                                                                                                                              | -    | 13      | -       |       |     |
|                                                                 |                     |                                                                                                                                   | Ch-2                                                                                                                              | -    | 40      | -       |       |     |
| Gate resistance                                                 | R <sub>g</sub>      | f = 1 MHz                                                                                                                         | Ch-1                                                                                                                              | 0.14 | 0.7     | 1.4     | Ω     |     |
|                                                                 |                     |                                                                                                                                   | Ch-2                                                                                                                              | 0.12 | 0.62    | 1.2     |       |     |
| Turn-on delay time                                              | t <sub>d(on)</sub>  | Channel-1<br>V <sub>DD</sub> = 15 V, R <sub>L</sub> = 3 Ω<br>I <sub>D</sub> ≅ 5 A, V <sub>GEN</sub> = 4.5 V, R <sub>g</sub> = 1 Ω | Ch-1                                                                                                                              | -    | 17      | 35      |       |     |
|                                                                 |                     |                                                                                                                                   | Ch-2                                                                                                                              | -    | 25      | 50      |       |     |
| Rise time                                                       | t <sub>r</sub>      |                                                                                                                                   | Channel-2<br>V <sub>DD</sub> = 15 V, R <sub>L</sub> = 3 Ω<br>I <sub>D</sub> ≅ 5 A, V <sub>GEN</sub> = 4.5 V, R <sub>g</sub> = 1 Ω | Ch-1 | -       | 40      |       | 80  |
|                                                                 |                     |                                                                                                                                   |                                                                                                                                   | Ch-2 | -       | 53      |       | 110 |
| Turn-off delay time                                             | t <sub>d(off)</sub> | Channel-1<br>V <sub>DD</sub> = 15 V, R <sub>L</sub> = 3 Ω<br>I <sub>D</sub> ≅ 5 A, V <sub>GEN</sub> = 4.5 V, R <sub>g</sub> = 1 Ω |                                                                                                                                   | Ch-1 | -       | 23      |       | 45  |
|                                                                 |                     |                                                                                                                                   |                                                                                                                                   | Ch-2 | -       | 30      |       | 60  |
| Fall time                                                       | t <sub>f</sub>      | Channel-1<br>V <sub>DD</sub> = 15 V, R <sub>L</sub> = 3 Ω<br>I <sub>D</sub> ≅ 5 A, V <sub>GEN</sub> = 4.5 V, R <sub>g</sub> = 1 Ω | Ch-1                                                                                                                              | -    | 7       | 15      |       |     |
|                                                                 |                     |                                                                                                                                   | Ch-2                                                                                                                              | -    | 12      | 25      |       |     |
| Turn-on delay time                                              | t <sub>d(on)</sub>  | Channel-2<br>V <sub>DD</sub> = 15 V, R <sub>L</sub> = 3 Ω<br>I <sub>D</sub> ≅ 5 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 1 Ω  | Ch-1                                                                                                                              | -    | 11      | 20      | ns    |     |
|                                                                 |                     |                                                                                                                                   | Ch-2                                                                                                                              | -    | 13      | 25      |       |     |
| Rise time                                                       | t <sub>r</sub>      |                                                                                                                                   | Ch-1                                                                                                                              | -    | 5       | 10      |       |     |
|                                                                 |                     |                                                                                                                                   | Ch-2                                                                                                                              | -    | 20      | 40      |       |     |
| Turn-off delay time                                             | t <sub>d(off)</sub> | Channel-2<br>V <sub>DD</sub> = 15 V, R <sub>L</sub> = 3 Ω<br>I <sub>D</sub> ≅ 5 A, V <sub>GEN</sub> = 10 V, R <sub>g</sub> = 1 Ω  | Ch-1                                                                                                                              | -    | 23      | 45      |       |     |
|                                                                 |                     |                                                                                                                                   | Ch-2                                                                                                                              | -    | 32      | 65      |       |     |
| Fall time                                                       | t <sub>f</sub>      |                                                                                                                                   | Ch-1                                                                                                                              | -    | 5       | 10      |       |     |
|                                                                 |                     |                                                                                                                                   | Ch-2                                                                                                                              | -    | 6       | 15      |       |     |



| SPECIFICATIONS (T <sub>J</sub> = 25 °C, unless otherwise noted) |                 |                                                                              |      |      |      |      |      |
|-----------------------------------------------------------------|-----------------|------------------------------------------------------------------------------|------|------|------|------|------|
| PARAMETER                                                       | SYMBOL          | TEST CONDITIONS                                                              |      | MIN. | TYP. | MAX. | UNIT |
| Drain-Source Body Diode Characteristics                         |                 |                                                                              |      |      |      |      |      |
| Continuous source-drain diode current                           | I <sub>S</sub>  | T <sub>C</sub> = 25 °C                                                       | Ch-1 | -    | -    | 44   | A    |
|                                                                 |                 |                                                                              | Ch-2 | -    | -    | 105  |      |
| Pulse diode forward current <sup>a</sup>                        | I <sub>SM</sub> |                                                                              | Ch-1 | -    | -    | 150  |      |
|                                                                 |                 |                                                                              | Ch-2 | -    | -    | 200  |      |
| Body diode voltage                                              | V <sub>SD</sub> | I <sub>S</sub> = 5 A, V <sub>GS</sub> = 0 V                                  | Ch-1 | -    | 0.75 | 1.1  | V    |
|                                                                 |                 | I <sub>S</sub> = 5 A, V <sub>GS</sub> = 0 V                                  | Ch-2 | -    | 0.44 | 0.7  |      |
| Body diode reverse recovery time                                | t <sub>rr</sub> | Channel-1<br>I <sub>F</sub> = 10 A, di/dt = 100 A/μs, T <sub>J</sub> = 25 °C | Ch-1 | -    | 36   | 75   | ns   |
|                                                                 |                 |                                                                              | Ch-2 | -    | 46   | 90   |      |
| Body diode reverse recovery charge                              | Q <sub>rr</sub> |                                                                              | Ch-1 | -    | 26   | 55   | nC   |
|                                                                 |                 |                                                                              | Ch-2 | -    | 40   | 80   |      |
| Reverse recovery fall time                                      | t <sub>a</sub>  | Channel-2<br>I <sub>F</sub> = 10 A, di/dt = 100 A/μs, T <sub>J</sub> = 25 °C | Ch-1 | -    | 16   | -    | ns   |
|                                                                 |                 |                                                                              | Ch-2 | -    | 18   | -    |      |
| Reverse recovery rise time                                      | t <sub>b</sub>  |                                                                              | Ch-1 | -    | 20   | -    |      |
|                                                                 |                 |                                                                              | Ch-2 | -    | 28   | -    |      |

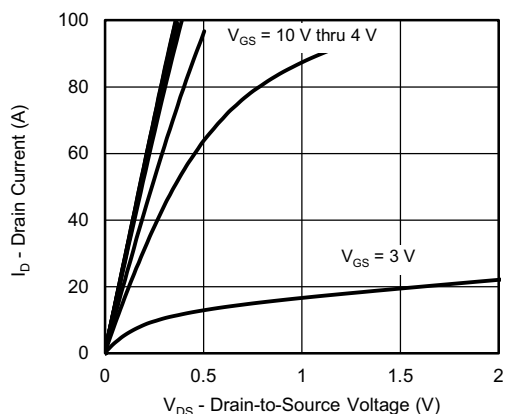
**Notes**

- a. Guaranteed by design, not subject to production testing  
b. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$

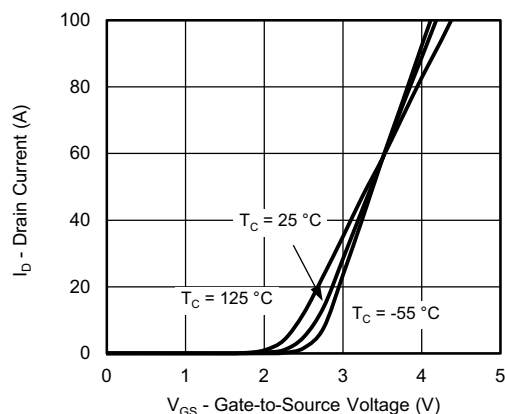
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



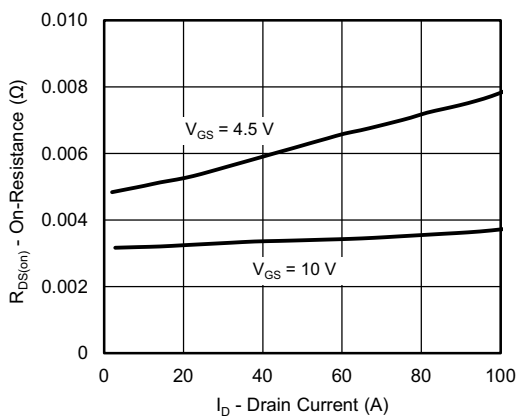
**CHANNEL-1 TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



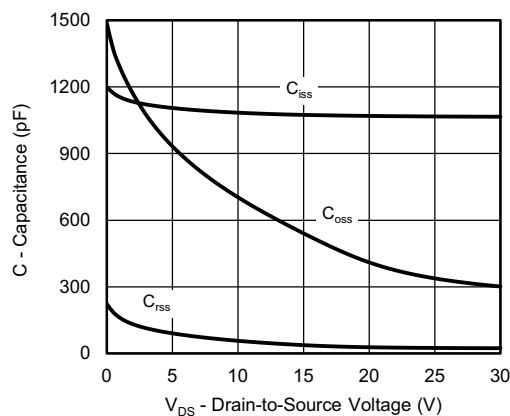
**Output Characteristics**



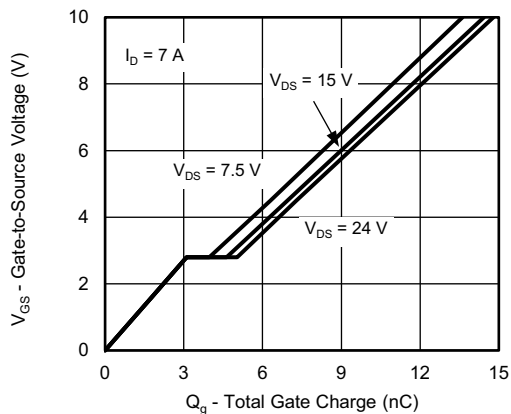
**Transfer Characteristics**



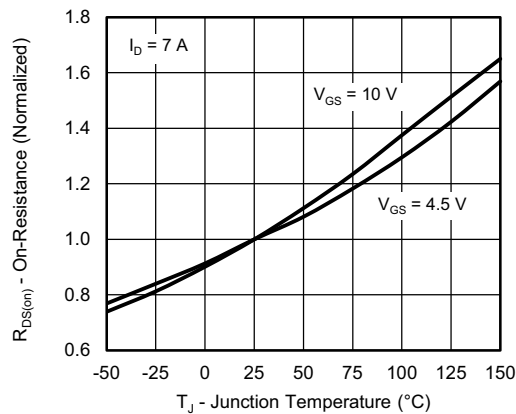
**On-Resistance vs. Drain Current**



**Capacitance**



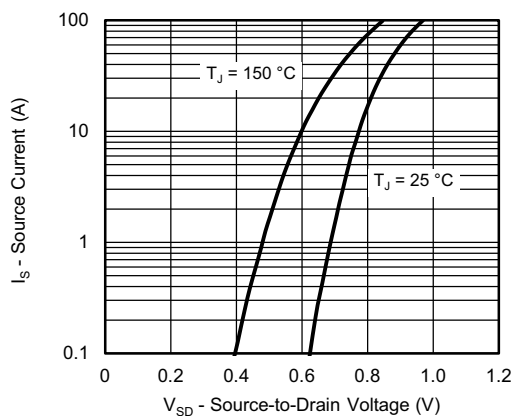
**Gate Charge**



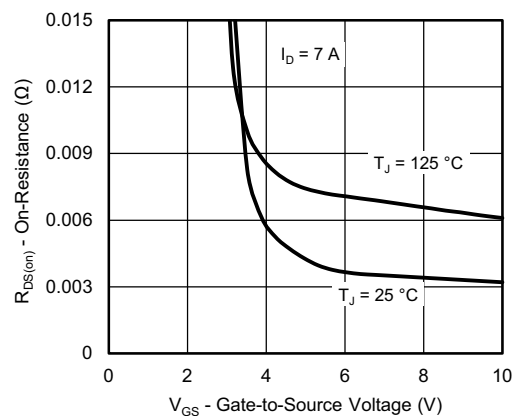
**On-Resistance vs. Junction Temperature**



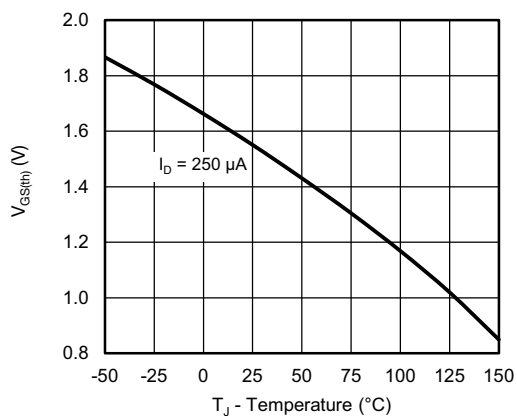
**CHANNEL-1 TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



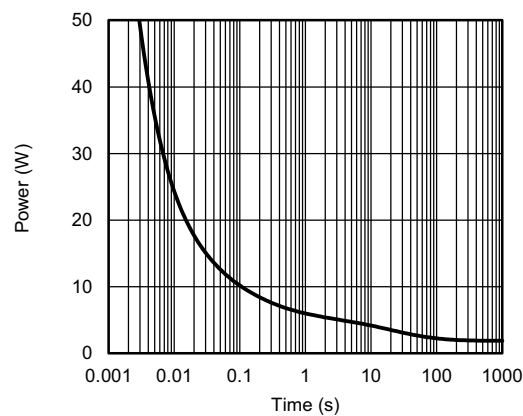
**Source-Drain Diode Forward Voltage**



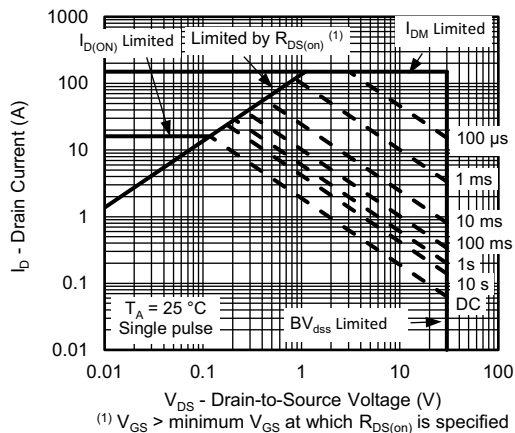
**On-Resistance vs. Gate-to-Source Voltage**



**Threshold Voltage**



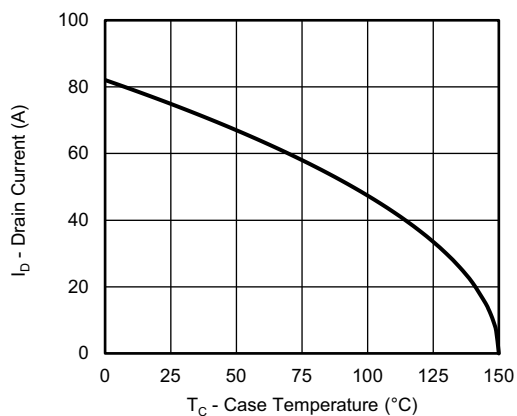
**Single Pulse Power, Junction-to-Ambient**



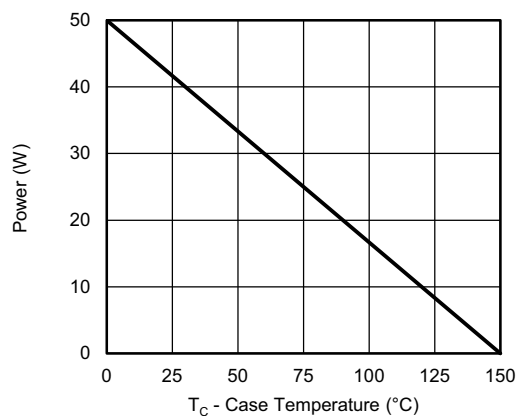
**Safe Operating Area, Junction-to-Ambient**



**CHANNEL-1 TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**Current Derating <sup>a</sup>**



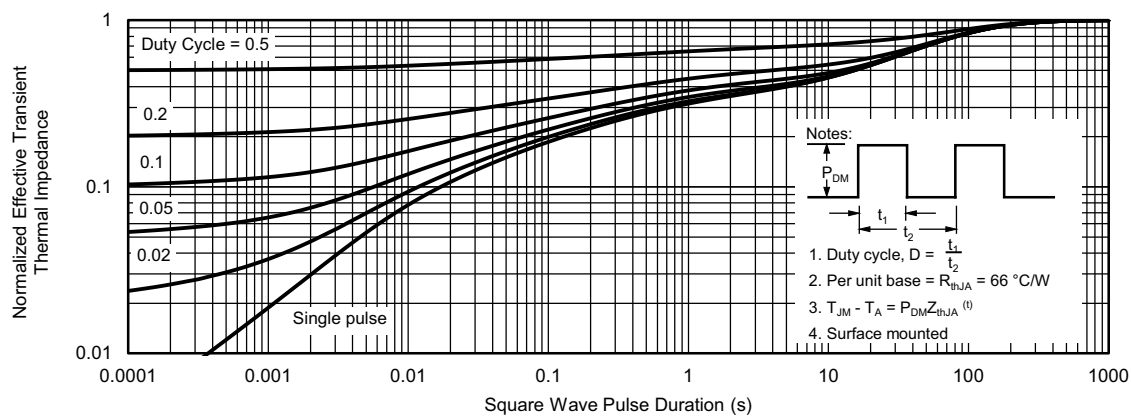
**Power, Junction-to-Case**

**Note**

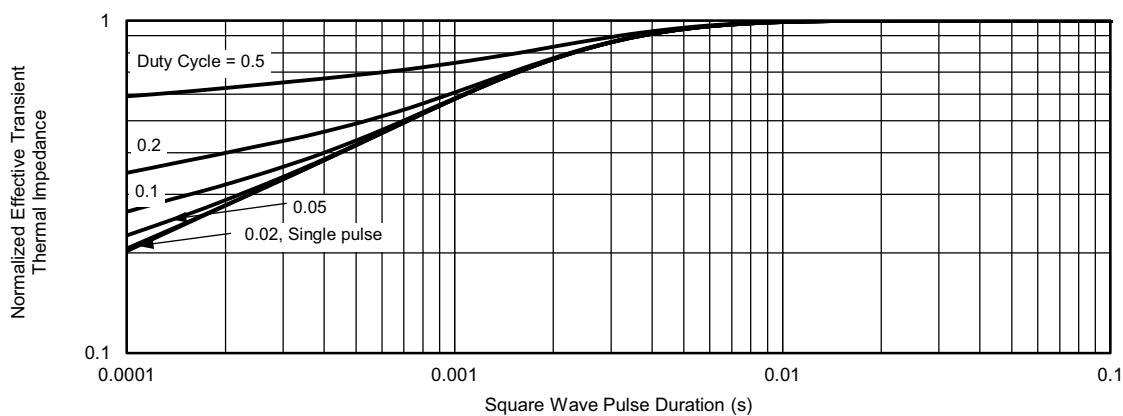
- a. The power dissipation  $P_D$  is based on  $T_J$  max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



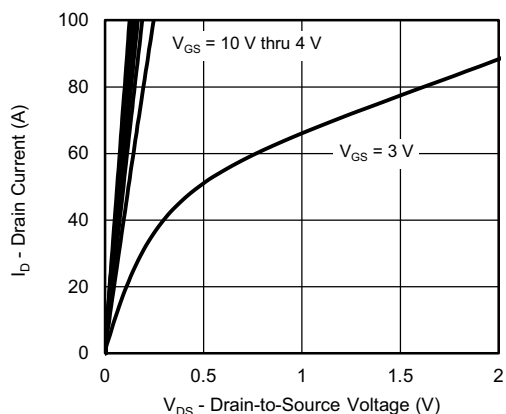
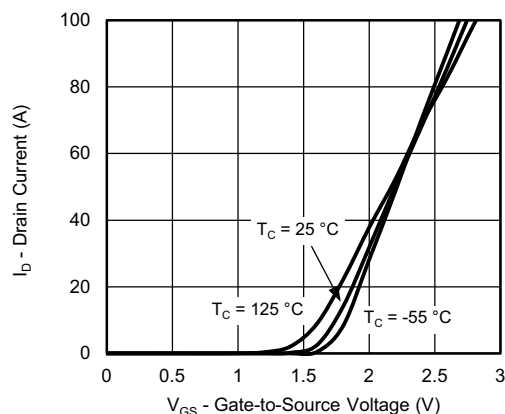
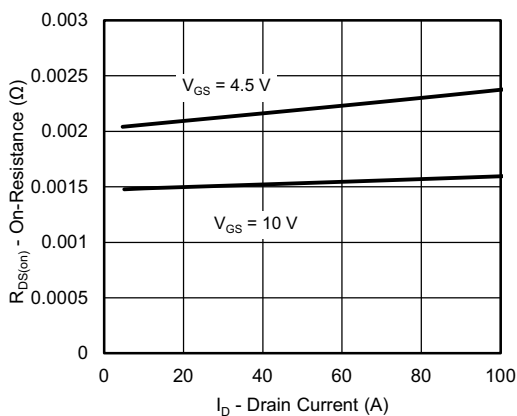
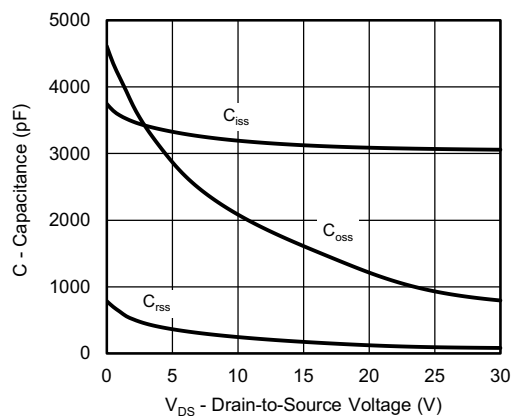
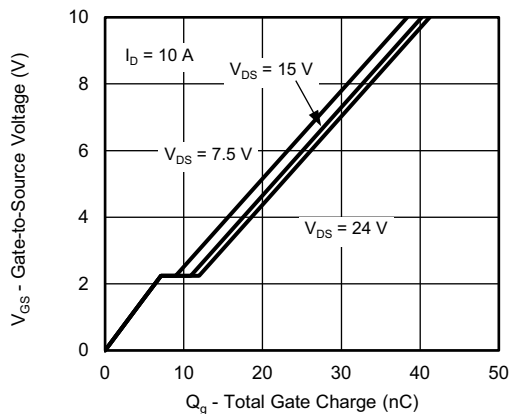
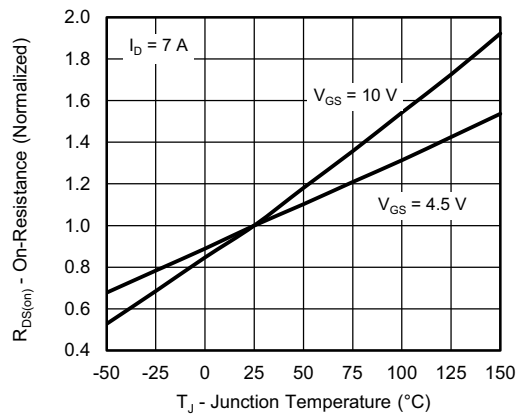
**CHANNEL-1 TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



**Normalized Thermal Transient Impedance, Junction-to-Ambient**

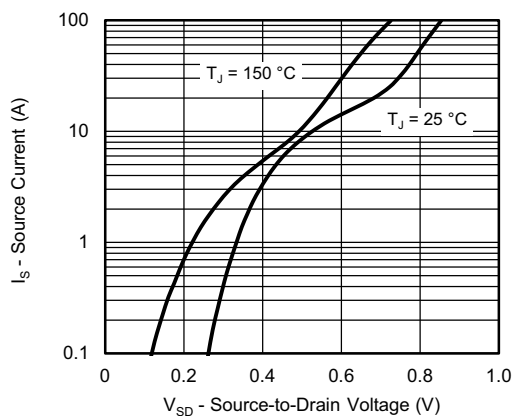


**Normalized Thermal Transient Impedance, Junction-to-Case**

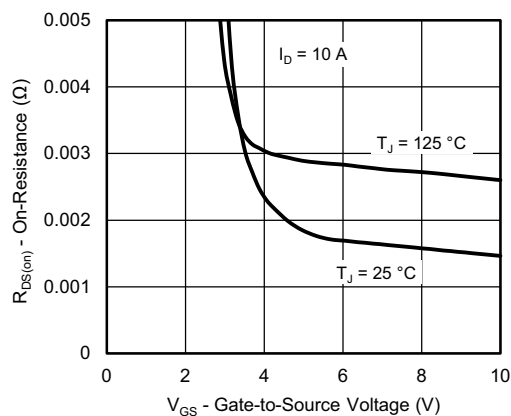
**CHANNEL-2 TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Output Characteristics**

**Transfer Characteristics**

**On-Resistance vs. Drain Current**

**Capacitance**

**Gate Charge**

**On-Resistance vs. Junction Temperature**



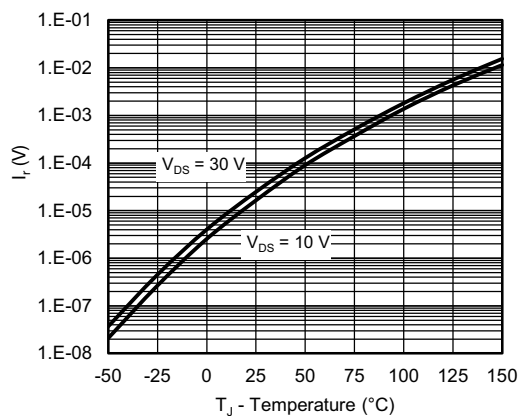
**CHANNEL-2 TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



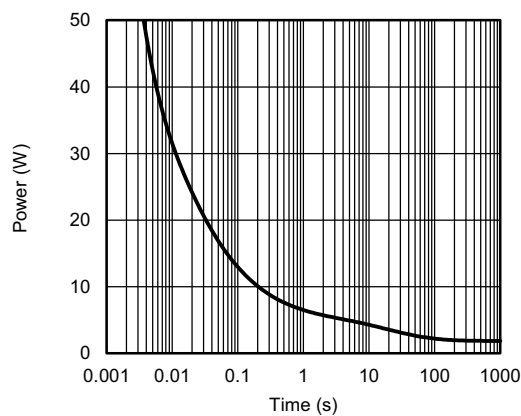
**Source-Drain Diode Forward Voltage**



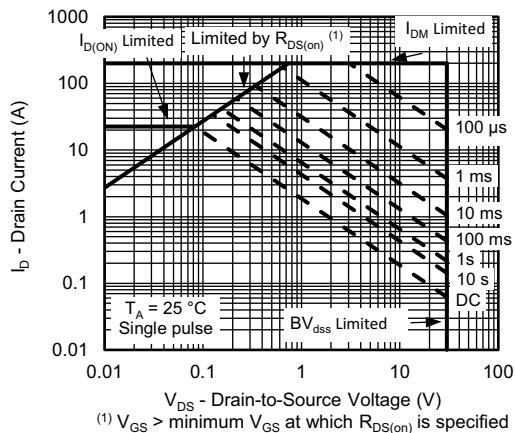
**On-Resistance vs. Gate-to-Source Voltage**



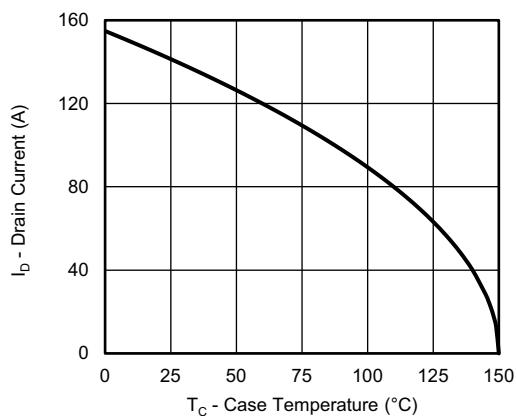
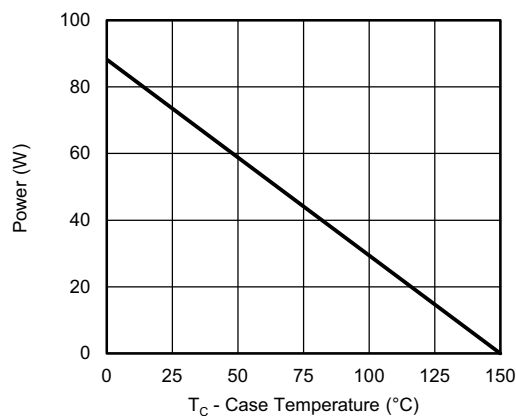
**Reverse Current (Schottky)**



**Single Pulse Power, Junction-to-Ambient**



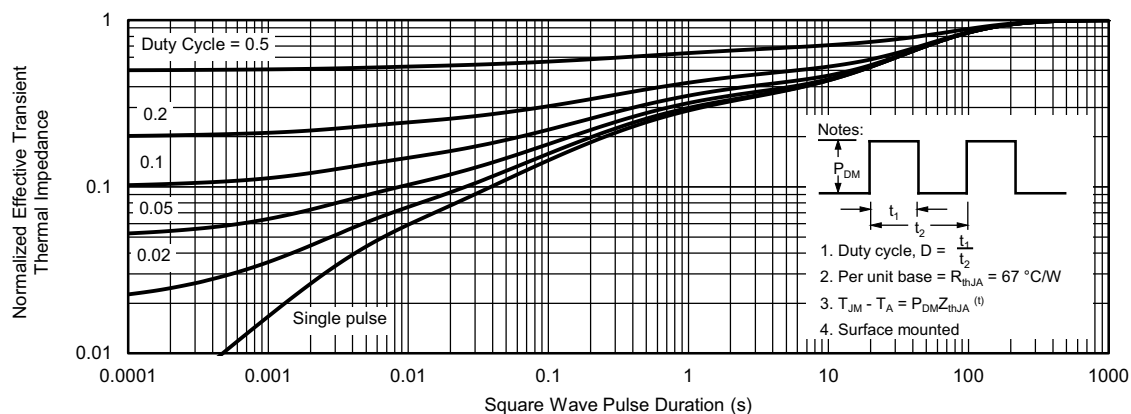
**Safe Operating Area, Junction-to-Ambient**

**CHANNEL-2 TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)

**Current Derating <sup>a</sup>**

**Power, Junction-to-Case**
**Note**

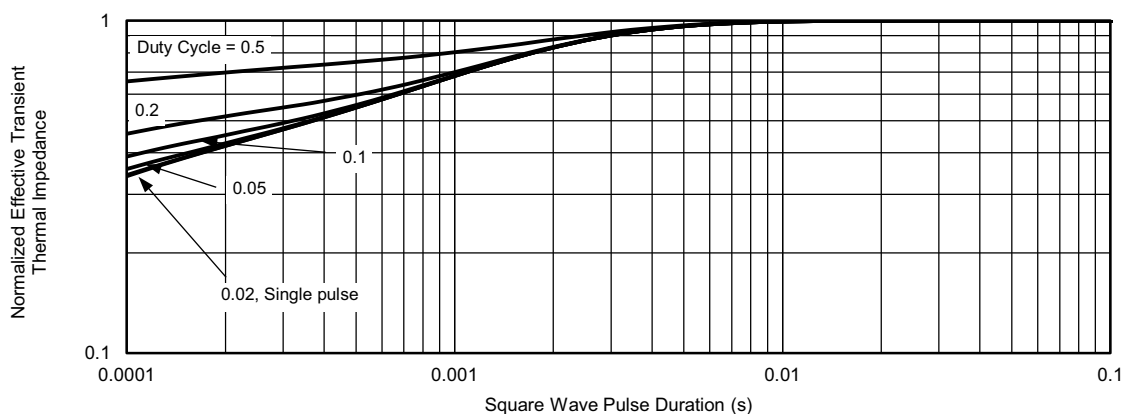
- a. The power dissipation  $P_D$  is based on  $T_J$  max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit



**CHANNEL-2 TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)



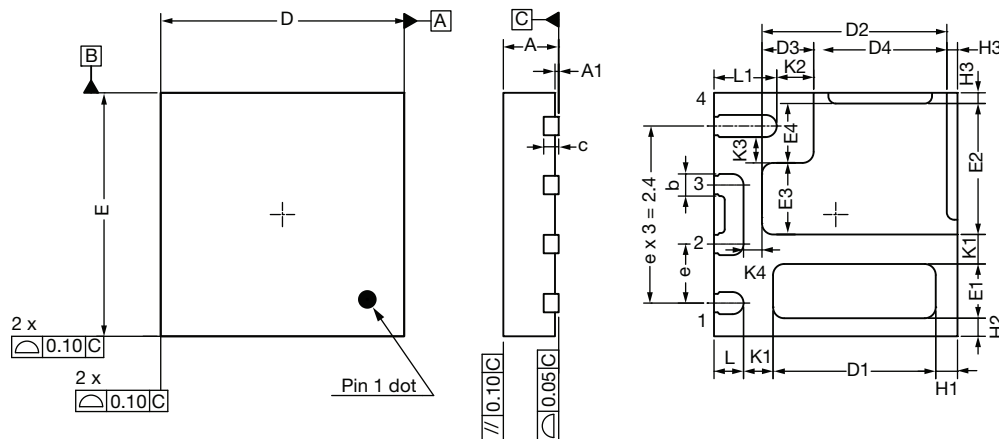
**Normalized Thermal Transient Impedance, Junction-to-Ambient**



**Normalized Thermal Transient Impedance, Junction-to-Case**

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see [www.vishay.com/ppg?76288](http://www.vishay.com/ppg?76288).

## PowerPAIR® 3 x 3F Case Outline



| DIM. | MILLIMETERS |      |      | INCHES     |       |       |
|------|-------------|------|------|------------|-------|-------|
|      | MIN.        | NOM. | MAX. | MIN.       | NOM.  | MAX.  |
| A    | 0.70        | 0.75 | 0.80 | 0.028      | 0.030 | 0.032 |
| A1   | 0.00        | 0.02 | 0.05 | 0.000      | 0.001 | 0.002 |
| b    | 0.25        | 0.30 | 0.35 | 0.010      | 0.012 | 0.014 |
| c    | 0.20 ref.   |      |      | 0.008 ref. |       |       |
| D    | 3.20        | 3.30 | 3.40 | 0.126      | 0.130 | 0.134 |
| D1   | 2.15        | 2.20 | 2.25 | 0.085      | 0.087 | 0.089 |
| D2   | 2.45        | 2.50 | 2.55 | 0.096      | 0.098 | 0.100 |
| D3   | 0.65        | 0.70 | 0.75 | 0.026      | 0.028 | 0.030 |
| D4   | 1.75        | 1.80 | 1.85 | 0.069      | 0.071 | 0.073 |
| E    | 3.20        | 3.30 | 3.40 | 0.126      | 0.130 | 0.134 |
| E1   | 0.69        | 0.74 | 0.79 | 0.027      | 0.029 | 0.031 |
| E2   | 1.73        | 1.78 | 1.93 | 0.068      | 0.070 | 0.072 |
| E3   | 0.92        | 0.97 | 1.02 | 0.036      | 0.038 | 0.040 |
| E4   | 0.76        | 0.81 | 0.86 | 0.030      | 0.032 | 0.034 |
| e    | 0.80 BSC    |      |      | 0.031 BSC  |       |       |
| K1   | 0.40 ref.   |      |      | 0.016 ref. |       |       |
| K2   | 0.50 ref.   |      |      | 0.020 ref. |       |       |
| K3   | 0.35 ref.   |      |      | 0.014 ref. |       |       |
| K4   | 0.25 ref.   |      |      | 0.010 ref. |       |       |
| H1   | 0.30 ref.   |      |      | 0.012 ref. |       |       |
| H2   | 0.25 ref.   |      |      | 0.010 ref. |       |       |
| H3   | 0.15 ref.   |      |      | 0.006 ref. |       |       |
| L    | 0.35        | 0.40 | 0.45 | 0.014      | 0.016 | 0.018 |
| L1   | 0.80        | 0.85 | 0.90 | 0.031      | 0.033 | 0.035 |

T18-0135-Rev. A, 02-Apr-18  
DWG: 6065

### Notes

- Use millimeters as the primary measurement
- Dimensioning and tolerances conform to ASME Y14.5M - 1994
- N is the number of terminals; Nd is the number of terminals in X-direction; Ne is the number of terminals in Y-direction
- Dimension b applies to plated terminal and is measured between 0.20 mm and 0.25 mm from terminal tip
- The pin # 1 identifier must be existed on the top surface of the package by using indentation mark or other feature of package body
- Exact shape and size of this features is optional
- Package warpage max. 0.08 mm
- Applied only for terminals



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